

CLAIM AMENDMENTS:

Please amend the claims as follows:

1. (Currently amended) A semiconductor laser comprising:
a substrate;
a semiconductor lamination portion including an active layer laminated on the substrate, the semiconductor lamination portion being made of a material having a cleavage plane not parallel to a cleavage plane of the substrate; and
a metal layer portion provided between on a layer that is above the substrate and under the active layer in a vicinity of on a resonance cavity end face and in a vicinity thereof.
2. (Original) The semiconductor laser according to claim 1, wherein the metal layer portion includes an element which is contained in the semiconductor lamination portion.
3. (Original) The semiconductor laser according to claim 1, wherein the metal layer portion is formed so as to have a width which is wider than that of a stripe-shaped portion for emitting and narrower than that of a semiconductor chip.
4. (Cancelled).

5. (Currently amended) A method for manufacturing a semiconductor laser comprising the steps of:

forming a semiconductor lamination portion including an active layer on a substrate, the semiconductor lamination portion being made of the material having a cleavage plane not parallel to a cleavage plane of the substrate,

forming a metal layer portion by melting a part of the semiconductor lamination portion, the part being above the substrate and under the active layer; and

forming resonance cavity end faces by cleaving the semiconductor lamination portion at the metal layer portion.

6. (Currently amended) The method for manufacturing the semiconductor laser according to claim 5, wherein the process of forming the metal layer portion is performed by irradiating a laser beam from a back surface of the substrate opposite to a surface laminated with the semiconductor lamination portion, and thereby melting [[a]] the part of the semiconductor lamination portion.

7. (Cancelled).